

Problems in realization of large-scale ensemble silicon-based NMR quantum computers

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Abstract

Problems in realization of silicon-based solid-state NMR quantum computer with ensemble addressing to qubits are considered. It is presented the extension of Kane's scheme to ensemble approach version with strip gates. For the initialization of nuclear quantum states it is proposed to use the solid-state effect in ENDOR technique whereby the nuclear spins can be practically fully polarized or, that is the same, indirect cooled to the spin temperature less than ~ 1 mK. It is suggested the possible planar silicon topology of such ensemble quantum computer and shown that the measurement with standard NMR methods signal of $L \sim 10^3$ qubit system may be achieved for a number of ensemble components $N \geq 10^5$. As another variant of ensemble silicon quantum computer the gateless architecture of cellular-automaton is also considered. The decoherence of quantum states in the ensemble quantum computers and ways of its suppression is also discussed.

Introduction

Atomic nuclei with a spin quantum number $I = 1/2$ seem to be the *natural candidates* for qubits — two-level quantum elements in quantum computers. The early approach to NMR quantum computers was suggested in 1997 [1, 2] and then confirmed in experiments [3, 4]. In this approach it was used several diamagnetic organic liquids which individual molecules, having a small number of interacted non-equivalent nuclear spins—qubits with $I = 1/2$ and being nearly independent one another. They act in parallel as an ensemble of *almost independent* quantum microcomputers.

Since in liquids the nuclear spins are very weakly coupled with the environment, the consideration may be restricted to nuclear spins of individual molecules (*reduced* quantum ensemble). For finite temperatures, the reduced ensemble is in the *mixed* state described by a density matrix.

Initialization of the nuclear spin states in this case means the separation of blocks from density matrix that must have properties similar to those of pure states (a pure-state diagonal matrix can have only one nonzero element). The states described by such matrix are called effective or *pseudo-pure* states. Several way of initialization have been reported in [1, 2, 4, 5].

The access to individual qubits in liquid sample is replaced by simultaneous access to related qubits in all molecules of a bulk ensemble. Computers of this type are called *bulk-ensemble* quantum computers. They, in principle, can operate at *room temperature*.

For measurements of qubit states the standard NMR technique is used. A principle one-coil scheme of experiment is shown in Fig.1. The sample is placed in the constant external magnetic field $\mathbf{B}$ and the alternating (say, linearly polarized) field $\mathbf{b}(t)$, produced by RF voltage $V_\omega(t)$:

$$\mathbf{B}(t) = \mathbf{B} + \mathbf{b}(t) = B\mathbf{k} + 2b \cos(\omega t + \varphi)\mathbf{i}, \quad (1)$$

where $\mathbf{i}$ and $\mathbf{k}$ are the unit vectors along the axes x and z.

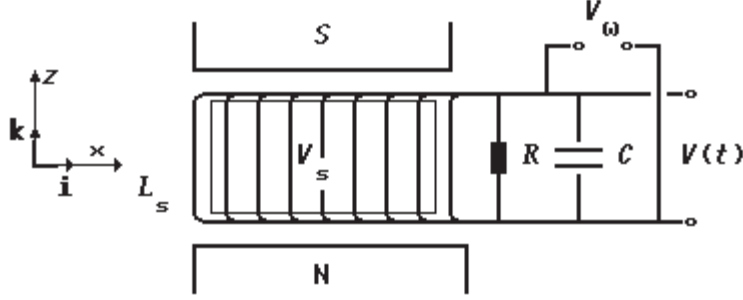


Fig. 1. The principle one-coil scheme of NMR measurement.

Let the sample be an ensemble of N molecules—microcomputers with L qubits at temperature $T = 300$ K, in the external magnetic fields $B = 1 - 10$ T. The resonance nuclear spin frequency is $\omega_A/2\pi \sim \gamma_I B/2\pi < 150$ MHz, γ_I is gyromagnetic ratio of nuclear spin ($\gamma_I \sim \gamma_N = 95.8$ radMHz/T), $\hbar\omega_A/kT < 10^{-5}$.

The output oscillating voltage $V(t)$ is

$$V(t) = QKd\Phi(t)/dt = \mu_0 QKA dM_x(t)/dt, \quad (2)$$

where $\Phi(t) = \int_A \mu_0 M_x(t) dx dz$ — magnetic flux produced by resonant spins in the coil, $L_s = \mu_0 (KA)^2/V$ — solenoid inductance of the resonance counter ($\mu_0 = 4\pi \cdot 10^{-1} \text{ T}^2 \text{ cm}^3/\text{J}$), V_s — volume of the solenoid, K — the number and A — area of coil turns, for resonance $\omega = \omega_A = (L_s C)^{-1/2}$, $Q = R/(\omega_A L_s) > 10^2$ — the *quality factor* of resonance counter in parallel connected resistance R (Fig.1).

The nuclear spin read-out magnetization M_x (the liquid sample is considered here as continuous medium) at optimum resonance conditions is defined by amplitude of RF field $b = 1/(\gamma_I \sqrt{T_{\perp I} T_{\parallel I}})$. For transverse $T_{\perp I}$ and longitudinal $T_{\parallel I}$ nuclear spin relaxation times $\sim 10^4$ s we have a value $b \sim 10^{-3}$ T and [6]

$$M_{x\max} = M_{z0} \sqrt{T_{\perp I}/T_{\parallel I}}/2 \approx \gamma_I \hbar/2 \cdot (N/V_s) \cdot \varepsilon(L)/2, \quad (3)$$

where N — number of resonant nuclear spins (one in a molecule) in volume V_s . Parameter $\varepsilon(L)$ is the maximum probability of the full nuclear polarization in pseudo-pure state $P_I = 1$ [7]. It may be estimated by the difference of equilibrium population between the lowest and highest energy states. For nearly homonuclear L spin system [7] it is ¹⁾:

$$\varepsilon(L) = \frac{\exp(L\hbar\omega_A/2kT) - \exp(-L\hbar\omega_A/2kT)}{(\exp(\hbar\omega_A/2kT) + \exp(-\hbar\omega_A/2kT))^L} = \frac{2 \sinh(L\hbar\omega_A/2kT)}{2^L \cosh^L(\hbar\omega_A/kT)}. \quad (4)$$

The other estimations of $\varepsilon(L)$ are given in [5].

In the high temperature limit $\hbar\omega_A/(kT) \ll 1$ we have $\varepsilon(L) = L2^{-L}\hbar\omega_A/(kT)$, that is, the signal *exponentially drops* with the number of qubits, but *does not* for $\hbar\omega_A/(kT) \gg 1$ when $\varepsilon(L) = 1$ (the pure nuclear quantum state).

¹⁾We have used here the two different notation for resonance frequency $\omega_A = \gamma_A B$ and $\omega_I = \gamma_I B$. They determinate accordingly values ε and M_{z0} in (2). For homonuclear diamagnetic liquids $\gamma_A = \gamma_I$.

The NMR signal intensity S is defined by amplitude

$$S = |V_{\max}| = (\mu_0/4) QKA(N/V_s)\gamma_I\hbar\omega_A\varepsilon(L), \quad (5)$$

The product KA can be expressed also as

$$KA = (L_s V_s / \mu_0)^{1/2} = (RV_s / (\mu_0 Q \omega_A))^{1/2}. \quad (6)$$

For the root-mean square noise voltage in the measurement circuit we become

$$V_N = \sqrt{4kTR\Delta\nu}, \quad (7)$$

where $\Delta\nu \sim 1 \text{ Hz}$ — the amplifier bandwidth.

So that for *signal to noise ratio* we obtain

$$\begin{aligned} (S/N) &\equiv |V_{\max}|/V_N \cong \frac{1}{8} \sqrt{\frac{\mu_0 \hbar Q \hbar \omega_A}{V_s \Delta\nu kT}} \gamma_I N \varepsilon(L) \sim \\ &\sim \sqrt{(Q/V_s) \cdot (\hbar \omega_A / kT)} N \varepsilon(L) \cdot 10^{-9}, \text{ (here } V_s \text{ in cm}^3\text{)}. \end{aligned} \quad (8)$$

For example, for two qubits molecules ($L = 2$), using, $\varepsilon(L) = \hbar \omega_A / (kT) \sim 10^{-5}$, we can make an estimate

$$(S/N) \sim (Q/V_s)^{1/2} N 10^{-17}. \quad (9)$$

Thus, the two qubits liquid ensemble at room temperature for $V_s \sim 1 \text{ cm}^3$ and $Q \sim 10^3$ is bounded by $N > 10^{16}$ molecules.

In the case of *paramagnetic liquids* one would expect that the number of molecules may be more increased with the use of a dynamic polarization (say, Overhauser effect). Assuming for electron and nuclear gyromagnetic ratio $\gamma_e/\gamma_I \sim 10^3$ we obtain that in the probability $\varepsilon(L)$ for a L -qubits single state the value $\hbar \omega_A / (kT) \ll 10^3$ should be replaced by $10^3 \hbar \omega_A / (kT)$. Therefore for the same value $\varepsilon(L)$ the allowed number of qubits L approximately will be estimated from

$$L 2^{-L} > 10^{-3}, \quad (10)$$

whence it follows that $L < 12$ qubits.

An additional increasing of read-out NMR signal in paramagnetic liquids may be obtained using the ENDOR technique. It is generally believed that for the liquid bull-ensemble quantum computers a *limiting value* is $L < 20 - 30$ [7].

However, for realization of *large-scale NMR quantum computers* a necessary number of qubits in quantum register must be $L > 10^3$, that may be attained only *at low temperatures in solid-state structures*.

The radically new and still unimplemented design of solid-state quantum computer was proposed in [8, 9]. It involves the formation of an multiple-spin system with access to *individual* nuclear spins—qubits. It was suggested to use an semiconductor MOS structure on a ^{28}Si spinless substrate, into a near-surface layer of which ^{31}P stable phosphorus isotopes, acting as donors, are implanted in form of regular chain. These donors have a nuclear spin $I = 1/2$ and substitute for silicon atoms at the lattice sites, producing shallow impurity states with a large effective Bohr radius. The number of donors or the qubit number L in a such quasi-one-dimensional *artificial "molecule"* may be

arbitrary large. It is suggested an electrical control and measurement of qubits states through the use of special gate structures.

The experimental implementation of Kane scheme is undertaken now in Australian Centre for Quantum Computer Technology [10].

There are four essential difficulties in implementing of quantum computer that was suggested by B. Kane in [8, 9]:

1) First of all, signal from the spin of an individual atom is very small and it is required of *high sensitive single-electron measurements*.

2) For initialization nuclear spin states it is required to use of *very low nuclear spin temperature* ($\sim$ mK).

3) It is required of regular donors and gates arrangement with high precision in *nanometer scale*.

4) It is necessary to suppress the *decoherence* of quantum states defined by *thermal fluctuations* of gate voltage.

As an alternative, the variant of *an ensemble silicon-based quantum computer* was proposed by us [11, 12]. One would expect that with the ensemble approach, where many independent "molecules" of Kane's type work simultaneously, the measurements would be greatly simplified. Here we will give a some further development of the scheme considered in [11, 12].

1 The silicon structure with regular system of strip gates

In this case, unlike the structure suggested in [8], gates **A** and **J** form a chain of narrow ($l_A \sim 10$ nm) and long strips along which donor atoms at l_y distant from each other are placed (Fig.2). Thus, they form a *regular* structure of the planar silicon topology type.

The separation between neighbourig donor atoms in Si, as in Kane's scheme, must be $l_x \leq 20$ nm). In this case the interqubit interaction is controlled by gates **J**. The depth of donor occurring $d \sim 20$ nm. For $l_y \gg l_x$ the exchange spin interaction between electrons of donor atoms along the strip gates (y -axis) is assumed negligibly small. Then, such a system breaks down into an ensemble of near-independent chains—Kane's artificial "molecule, whose electronic spins at temperature $T \leq 0,1$ K are initially fully aligned with the field of several Tesla ($\gamma_e \hbar B / kT \gg 1$). The linear qubit density in artificial "molecules" is ~ 50 qubits on micrometer.

For *the initializing* of all nuclear spins-qubit quantum states (fully polarized nuclear spins) there is a need to attain, for the time being, spin temperature $T \leq 10^{-3}$ K. An output signal in this system, as in liquids, will be proportional to the number of the "molecules" or donor atoms N (components of our ensemble) in the chain along axis y .

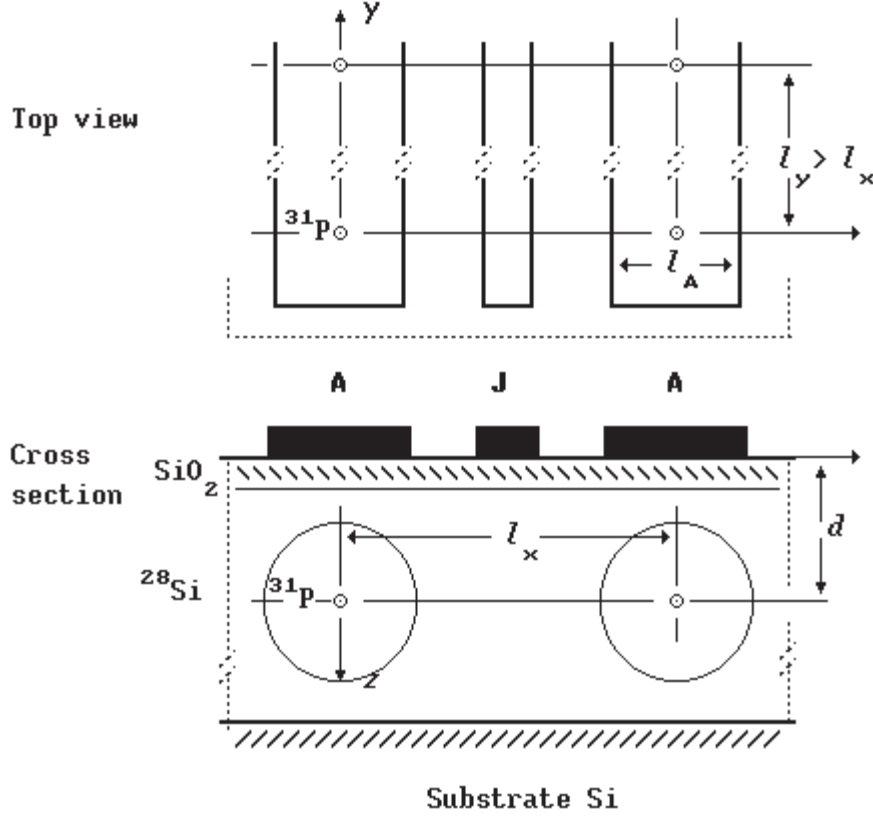


Fig. 2. The silicon structure (^{28}Si) with donors atoms ^{31}P and strip gates (Al).

However for the realization of considered structure with donor chains and parallel strip gates, as well as of the Kane's scheme, *the nanotechnology* with resolving of order ~ 1 is also needed. We will not discuss here the technology problems in realizing of the suggested silicon-based structure (see [10]).

2 The states of insulated donor atoms in magnetic fields

The electron-nuclear spin Hamiltonian for a donor atom ^{31}P has the form

$$\hat{H} = \gamma_e \hbar \mathbf{B} \hat{\mathbf{S}} - \gamma_I \hbar \mathbf{B} \hat{\mathbf{I}} + A \hat{\mathbf{I}} \hat{\mathbf{S}}, \quad (11)$$

four energy levels of which are given by the well-known Breit-Rabi's formula. For $I = 1/2$, $S = 1/2$ (the z -axis is parallel to $\mathbf{B}$) this formula is written as

$$E(F, m_F) = -\frac{A}{4} - \gamma_I \hbar B m_F - (-1)^F \frac{A}{2} \sqrt{1 + 2m_F X + X^2}, \quad (12)$$

where constant of hyperfine interaction $A/(2\pi\hbar) = 116 \text{ MHz}$ [13], $X = (\gamma_e + \gamma_I)\hbar B/A \approx \gamma_e \hbar B/A$, $F = I \pm 1/2 = 1, 0$, and $m_F = M + m = \pm 1, 0$, if $F = 1$ or $m_F = 0$, if $F = 0$ (Here $M = \pm 1/2$ and $m = \pm 1/2$ are z -projections of electronic and nuclear spins accordingly). The energy levels are shown in Fig. 3. For the energy of the ground spin state, $F = 0$ and $m_F = 0$, hence, we obtain

$$E(0, 0) = -A/4 - (A/2)\sqrt{1 + X^2}. \quad (13)$$

For the next, excited energy state, $F = 1$, $m_F = -1$ we have

$$E(1, -1) = A/4 - (\gamma_e - \gamma_I)\hbar B/2. \quad (14)$$

Thus, the energy difference between the two states of the nuclear spin that interacts with an electron, whose state remains unchanged, is described in simple terms ($\gamma_e \gg \gamma_I$ for $X \approx \gamma_e \hbar B/A \gg 1$):

$$\begin{aligned} \hbar\omega_A^+ &= E(1, -1) - E(0, 0) = A/2 + (\gamma_I - \gamma_e)\hbar B/2 + \frac{A}{2}\sqrt{1 + X^2} \approx \\ &\approx \gamma_I \hbar B + \frac{A}{2} - \frac{A^2}{4\gamma_e \hbar B}, \\ \hbar\omega_A^- &= E(1, 1) - E(1, 0) \approx -\gamma_I \hbar B + \frac{A}{2} + \frac{A^2}{4\gamma_e \hbar B}. \end{aligned} \quad (15)$$

For ^{31}P donor atoms $\gamma_e/\gamma_I = 1.62 \cdot 10^3$, $\gamma_e = 176.08 \text{ radGHz/T}$, $\gamma_I = 1.13\gamma_N = 108 \text{ radMHz/T}$. In magnetic field $B = 1 \text{ T}$: $\omega_A^+/2\pi = 75 \text{ MHz}$, $\omega_A^-/2\pi = 41 \text{ MHz}$.

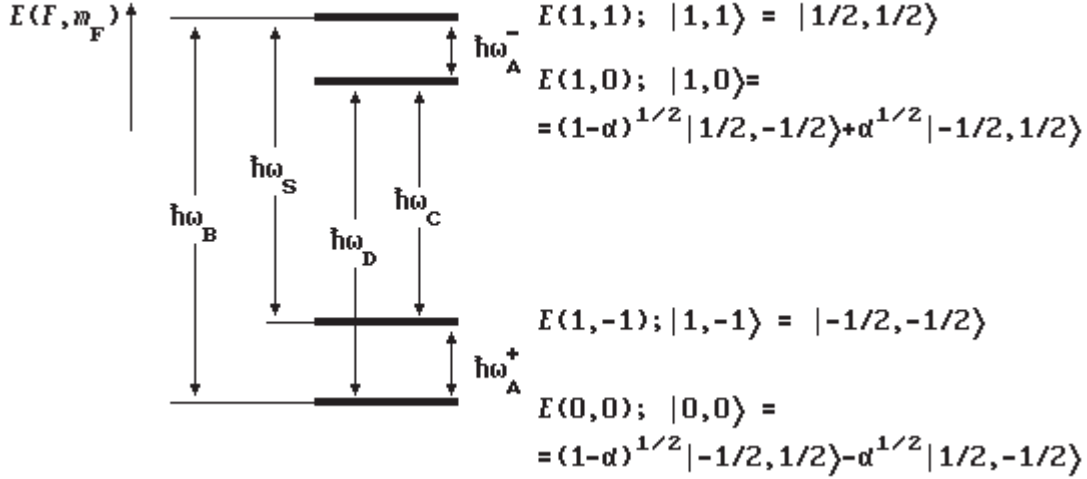


Fig. 3. Energy levels of an individual donor atom in magnetic field. The frequencies $\omega_S = \omega_B - \omega_A^+$, ω_B , ω_C , $\omega_D = \omega_B - \omega_A^-$ are in microwave, $\omega_A^\pm$ – in the RF range of frequencies. The transitions with frequencies ω_B , ω_D , ω_C , $\omega_A^\pm$ are *allowed*, but transitions with frequencies ω_S in the first approximation are *forbidden*.

The state $|1, -1\rangle$ in M, m basis is equivalent to state $|M = -1/2, m = -1/2\rangle$ and state $|0, 0\rangle$ in this basis is the following singlet superposition of states

$$|0, 0\rangle = (1 - \alpha)^{1/2}|-1/2, 1/2\rangle - \alpha^{1/2}|1/2, -1/2\rangle,$$

$$\alpha = \frac{1}{2} \left(1 - \frac{X}{\sqrt{1 + X^2}} \right) \quad (16)$$

The diagonal matrix elements of nuclear magnetization M_{z0} for two lower energy states will be determined by

$$\langle 0, 0 | M_{z0} | 0, 0 \rangle = \langle 0, 0 | I_z | 0, 0 \rangle \gamma_I \hbar = \frac{X}{\sqrt{1 + X^2}} \gamma_I \hbar / 2,$$

$$\langle 1, -1 | M_{z0} | 1, -1 \rangle = \langle 1, -1 | I_z | 1, -1 \rangle \gamma_I \hbar = -\gamma_I \hbar / 2. \quad (17)$$

The populations of the L -qubit lowest and highest energy states for $M = -1/2$, which give, as noted above, the maximum probability of the full nuclear polarisation in pseudo-pure state, are:

$$p(1, -1) = \frac{\exp(-L\hbar\omega_A^+/2kT)}{(\exp(\hbar\omega_A^+/2kT) + \exp(-\hbar\omega_A^+/2kT))^L},$$

$$p(0, 0) = \frac{\exp(L\hbar\omega_A^+/2kT)}{(\exp(\hbar\omega_A^+/2kT) + \exp(-\hbar\omega_A^+/2kT))^L}. \quad (18)$$

The maximum nuclear magnetization M_{z0} (the populations of states (1,1) and (1,0) are negligible for $\omega_S, \omega_B, \omega_C \gg \omega_A^\pm$) is

$$M_{z0} = \gamma_I \hbar / 2 \cdot (N/V_c) \left\{ \frac{X}{\sqrt{1+X^2}} \frac{\exp(L\hbar\omega_A^+/2kT)}{(\exp(\hbar\omega_A^+/2kT) + \exp(-\hbar\omega_A^+/2kT))^L} - \frac{\exp(-L\hbar\omega_A^+/2kT)}{(\exp(\hbar\omega_A^+/2kT) + \exp(-\hbar\omega_A^+/2kT))^L} \right\}. \quad (19)$$

For $L\hbar\omega_A^+/2kT \ll 1$ and $X \gg 1$ we obtain (compare with (3))

$$M_{z0} \approx \gamma_I \hbar / 2 \cdot (N/V_c) \cdot 2^{-L} L (\hbar\omega_A^+/kT). \quad (20)$$

But for very low temperatures ($\hbar\omega_A^+/2kT \gg 1$) we have the *full nuclear polarization*: $M_{z0} \approx \gamma_I \hbar / 2 \cdot (N/V_c)$ and $\varepsilon(L) = 1$.

3 The gain effect for NMR signal

Transitions between two lower states are induced by a RF magnetic field, applied at a frequency resonant ω_A . The Rabi resonance frequency Ω , which is defined by matrix elements of spin interaction Hamiltonian with the external RF field $\mathbf{b}(t)$

$$\hat{H}_{\text{rf}} = \left(\gamma_e \hat{S}_x - \gamma_I \hat{I}_x \right) \hbar \cdot \mathbf{b}_x(t), \quad (21)$$

can be found from

$$\Omega = \gamma_I b_{\text{eff}}(X) = 2 |\langle 0, 0 | \hat{H}_{\text{rf}} | 1, -1 \rangle| / \hbar. \quad (22)$$

For the amplitude of effective RF field, acting on nuclear spin, $b_{\text{eff}}(X)$ we obtain

$$b_{\text{eff}}(X) = b \left(\alpha^{1/2} \gamma_e / \gamma_I + (1 - \alpha)^{1/2} \right), \quad (23)$$

where b — the amplitude of circularly polarized field component.

The Rabi frequency has the maximum value for $X = 0$ and rapidly monotonic reduce to value for insulated nuclear spin ($A \Rightarrow 0$), $\gamma_I b_{\text{eff}}(X) \gg 1$) = $\gamma_I b$. From a rate of quantum operation standpoint it is desirable to operate in the relatively weak fields, at which $\gamma_e / \gamma_I \gg X \approx \gamma_e \hbar B / A \gg 1$ or $3.5T > B \gg 3.9 \cdot 10^{-3} \text{ T}$.

In this case from (23) we will obtain

$$b_{\text{eff}} = (1 + \eta)b \gg b, \quad (24)$$

where $\eta = A/(2\gamma_I \hbar B) \gg 1$ is the *gain factor*. On these conditions RF field operate through the transverse component of electronic polarization. For magnetic fields $B = 1 \text{ T}$ we have the value $b_{\text{eff}} = 4.4 \cdot b$, and for $B = 0.01 \text{ T}$ – value $b_{\text{eff}} = 338 \cdot b$.

The gain effect involves an increase of NMR signal and Rabi frequency. In the pulse technique it make possible *to decrease the length of pulse*. This effect was first indicated by Valiev in [14]. The computer operations, owing to this effect, can be done at lower RF fields. At last, it permits *to reduce the RF field influence* on the operation of neighbour semiconductor devices.

To describe the nuclear dynamics of the studied two low-lying levels system we can write the followed Bloch-type equation:

$$\frac{d\mathbf{M}}{dt} = \gamma_I [\mathbf{M} \times \mathbf{B}_{\text{eff}}] - \frac{M_x \mathbf{i} + M_y \mathbf{j}}{T_{\perp I}} - \frac{(M_z - M_{z0}) \mathbf{k}}{T_{\parallel I}}, \quad (25)$$

where $\mathbf{i}, \mathbf{j}, \mathbf{k}$ are orthogonal unit vectors (Fig.1),

$$\mathbf{B}_{\text{eff}} = (\omega_A/\gamma_I) \mathbf{k} + 2b_{\text{eff}} \cos(\omega t) \mathbf{i}, \quad (26)$$

from where it follows that the value of maximum nuclear read-out magnetization in NMR signal, which there have been here for $b_{\text{eff}}(X) = 1/(\gamma_I \sqrt{T_{\perp I} T_{\parallel I}})$, again have value $M_x = M_{z0}/2$. That is, the read-out *NMR signal can not be increased* through the gain effect over its maximum value $M_{z0}/2$, but it *can be achieved at more lower* RF fields than in the absent of gain effect.

4 The signal to noise ratio for an ensemble silicon quantum computer

For the realization of an ensemble silicon quantum register we propose a variant of planar scheme, that contains $n \cdot p$ in parallel acting blocks, each have N_0 in parallel connected L -qubit Kane's linear "molecules". This scheme is schematically depicted at Fig. 4.

Let the sample be the silicon (^{28}Si) plate of thick $\delta \sim 0.1 \text{ cm}$. For the full number of computers-"molecules" in ensemble $N = p \cdot N_0 \cdot n$, the volume of sample and also of solenoid is $V_s \approx \delta \cdot l_x \cdot l_y \cdot L \cdot N$ (the filling factor is assumed to be approximately one).

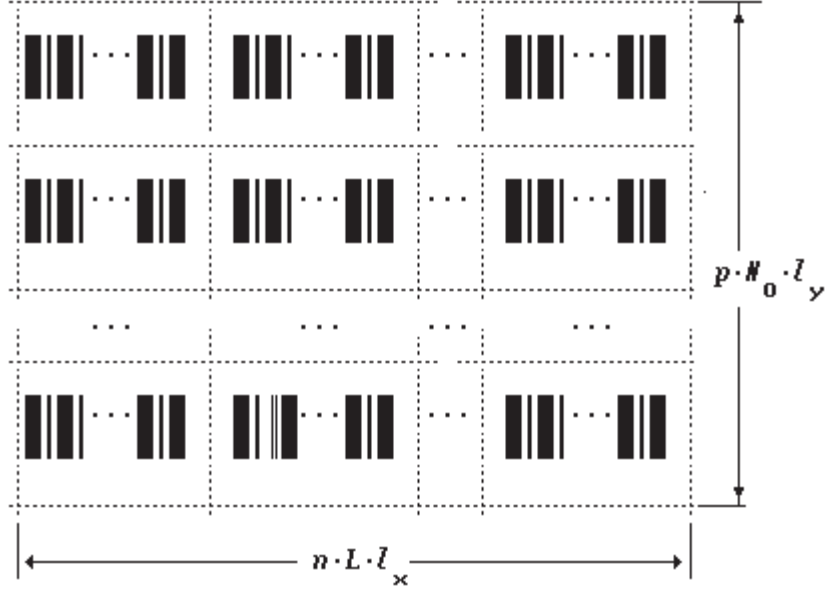


Fig. 4. The scheme of the planar silicon topology with $p \cdot n$ in parallel connected blocks of the ensemble L -qubit quantum computers (the connections are not shown here). The broad and narrow lines denote the **A** and **J** gates.

The read-out signal from the such *ensemble in parallel acting* chains, as distinct from liquid prototype, for full nuclear polarization or, what is the same, for spin temperatures $T_1 \leq 10^{-3}$ K has no small factor in intensity of the NMR signal of type $\varepsilon(L) = 2^{-L} L \cdot \hbar\omega_A/(kT)$. The NMR signal from our sample within of a non-essential factor is the same as from macroscopic sample (see Appendix). Therefore, with the expression (8), $\hbar\omega_A/(kT) \sim 10^{-2}$ ($T \sim 0.1$ K) and $\varepsilon = 1$ we will obtain as an estimation

$$(S/N) \approx \sqrt{Q\hbar\omega_A/(kTV_s)} \cdot N \cdot 10^{-9} \approx \sqrt{QN/(\delta l_x l_y L)} \cdot 10^{-10}. \quad (27)$$

It is believed that for superconducting Al gates it is possible $Q \sim 10^6$. The effective volume of one "molecule" for $l_x = 20$ nm, $l_y = 50$ nm, $L = 10^3$, $V_s = \delta l_x l_y L = 10^{-9}$ cm³ we receive that the read-out signal in our scheme may be *available for standard NMR technique* if the number of "molecules" in ensemble will be $N \geq 10^5$. High-sensitive devices for individual measurements are not needed.

To estimate the values n , p let us consider the square sample with $50N_0p = 20 \cdot 10^3 n$ and $N_0 = 100$. As a result, we receive $n \approx 16$ and $p \approx 63$. The area of the structure is $\sim 315 \times 315$ μm^2 . This size is sufficiently small for sample to be housed in the split between the magnet poles of a NMR spectrometer.

For implementation of two-qubit logic operation it is required the controlled by gates **J** interqubit indirect interaction with characteristic frequency $\nu_J \sim 100$ kHz $\ll \omega_A/2\pi \sim 100$ MHz. To bring about fault-tolerant quantum computations the relative error for single logic operation must be no more then $\sim 10^{-5}$ [15]. Hence it follows that a *resolution* bound of the NMR spectrometer must be of order $\sim 100 \text{ kHz} \cdot 10^{-5} \sim 1$ Hz, that is consistent with the usual requirements. Notice that such high precision is needed only for performing the logic quantum operation, but it is not needed for read-out measurements.

The read-out signal may be some more increased by means of an electron-nuclear double resonance (ENDOR) methods [16] of observing the electron resonance at transition with frequencies ω_B and ω_C (Fig. 3).

Consequently, by use of standard NMR and additional of ENDOR techniques *the first main difficulty* of Kane's scheme can be overcome.

5 The longitudinal relaxation times and long-lived nonequilibrium quantum states

The electron and nuclear *longitudinal relaxation times* for the *allowed* transitions in four energy levels system of phosphorus doped silicon have been extensively investigated experimentally in [16], see also [17]. For the allowed transitions with frequency ω_B and ω_C (Fig.3) electron longitudinal relaxation times $T_{||B} \approx T_{||C}$ at low temperatures was found to be exceedingly long. They are of order *one hour* at $T = 1.25$ K, $B \sim 0,3$ T, are independent of phosphorus concentration below $C \sim 10^{16} \text{ cm}^{-3}$ and are approximately inversely proportional to lattice temperature T . But they very fast drops to ~ 1 s already at $C \sim 10^{17} \text{ cm}^{-3}$. For the structure on Fig.2 $d = 20$ nm, $l_x = 20$ nm, $l_y = 50$ nm we obtain the average distance between atoms ^{31}P in silicon $l_{av} = (20 \cdot 20 \cdot 50)^{1/3} = 27$ nm and their associated concentration $C = (l_{av})^{-3} = 5 \cdot 10^{16} \text{ cm}^{-3}$. For this value of C according to [16] we must have $T_{||B} \sim 100$ s.

The further increasing the electron relaxation times may be achieved by decreasing of lattice temperature. It is possible to extrapolate electron relaxation time to $T \sim 0.1$ K resulting in a value $T_{||B} \sim 1000$ s.

The relaxation time for transition with frequency ω_D , which involves a simultaneous electron-nuclear spin flip-flop, at $T = 1.25$ K, $C \sim 10^{16} \text{ cm}^{-3}$ and $B \sim 0,3$ T was $T_{||D} \sim 30$ hours $\gg T_{||B}, T_{||C}$.

The nuclear longitudinal relaxation time $T_{||I}$ exceed 10 hours [15]. Notice, that *for full electronic polarization*, occurring at $T \leq 0,1$ K, this time *does not depend on the interaction with neighbour electron spins* [17].

The dipole-dipole interaction of separated qubits in our chains with polarized electron spins of neighbours phosphorus atoms is divided into *secular* and *nonsecular* parts. The main part of it is the secular part. It lead up to constant shift of resonance nuclear frequencies of order $\mu_0 \gamma_N \gamma_B \hbar / (4\pi l_x^3) \sim 10$ Hz, where $\gamma_B = 2\mu_B / \hbar = 176 \text{ radGHz/T}$, $l_x \sim 20$ nm.

To suppress the influence of the unwanted secular part of dipole-dipole spin interaction in a chain, may be applied the external magnetic field, $\mathbf{B}$, at an "magic" angle, $\theta = \arccos(1/\sqrt{3}) = 54.74^\circ$ to direction of the chain.

The *extremely long relaxation times* of the electron and nuclear spins imply that the required initializing of nuclear quantum states (full nuclear *nonequilibrium polarizations*) can be attained by deep cooling of short duration *only nuclear spin system* to $T \leq 1$ mK without deep cooling of lattice. There is the possibility to reach it at *indirect cooling* of nuclear spin system by means of *dynamic nuclear spin polarization techniques* [17].

6 The cooling of nuclear spin system and initialization nuclear states by means of dynamic polarization

One such method of dynamic nuclear spin polarization for donor atoms is based on the saturation by *the microwave pumping of the forbidden transition* (frequency ω_S in Fig.3), that is designated as the *solid state effect* [6, 17].

Let us consider this effect. The polarizations of electrons $P_S = 2\langle S_z \rangle$ and of nuclei $P_I = 2\langle I_z \rangle$ can be expressed as

$$P_S = p(1, 1) + p(1, 0) - p(1, -1) - p(0, 0), \quad (28)$$

$$P_I = p(1, 1) + p(0, 0) - p(1, 0) - p(1, -1),$$

where $p(F, M_F)$ are the populations of states F, M_F (Fig.3). They fill also the requirement

$$p(1, 1) + p(1, 0) + p(1, -1) + p(0, 0) = 1. \quad (29)$$

Let us write the rate equations for the populations:

$$\begin{aligned} dp(0, 0)/dt &= (p(1, 1) - p(0, 0)r_B)/T_{\parallel B} + (p(1, 0) - p(0, 0)r_D)/T_{\parallel D} + \\ &\quad + (p(1, -1) - p(0, 0)r_A^+)/T_{\parallel A}, \\ dp(1, -1)/dt &= (p(1, 0) - p(1, -1)r_C)/T_{\parallel C} + (p(1, 1) - p(1, -1)) \cdot W_e + \\ &\quad + (p(0, 0)r_A^+ - p(1, -1))/T_{\parallel A}, \\ dp(1, 0)/dt &= (p(1, -1)r_C - p(1, 0))/T_{\parallel C} + p(0, 0)r_D - p(1, 0))/T_{\parallel D} + \\ &\quad + (p(1, 1) - p(1, 0)r_A^-)/T_{\parallel A}, \\ dp(1, 1)/dt &= (p(0, 0)r_B - p(1, 1))/T_{\parallel B} + (p(1, -1) - p(1, 1)) \cdot W_e + \\ &\quad + (p(1, 0)r_A^- - p(1, 1))/T_{\parallel A} \end{aligned} \quad (30)$$

where parameters $r_{B,C,D,A} = \exp(-\hbar\omega_{B,C,D,A}/kT)$ are ratio of rates for a up and down thermal transitions. For values $\hbar\omega_{B,C,D}/kT \gg 1$, $\hbar\omega_A^\pm/kT \ll 1$ ($T \leq 0,1$ K) there are the thermal electron $P_{S0} = -1$ and nuclear $P_{I0} = \hbar\omega_A^+/kT \ll 1$ polarizations.

Let us propose next that rate W_e of *the induced forbidden electron transitions* $|1, 1\rangle \Rightarrow |1, -1\rangle$ and electron longitudinal relaxation times are satisfied the conditions: $W_e^{-1} < T_{\parallel B} \approx T_{\parallel C}, T_{\parallel A} \ll T_{\parallel D} < T_{\parallel S}$ ($T_{\parallel S}$ is the longitudinal relaxation time of electron spins for forbidden transition). Hereafter we shall write

$$\begin{aligned} dp(0, 0)/dt &= p(1, 1)/T_{\parallel B} + (p(1, -1) - p(0, 0))/T_{\parallel A}, \\ dp(1, -1)/dt &= p(1, 0)/T_{\parallel B} + ((p(1, 1) - p(1, -1)) \cdot W_e + \\ &\quad + (p(0, 0) - p(1, -1))/T_{\parallel A}, \end{aligned}$$

$$\begin{aligned}
dp(1,0)/dt &= -p(1,0)/T_{\parallel B} + (p(1,1) - p(1,0))/T_{\parallel A} + \\
dp(1,1)/dt &= -p(1,1)/T_{\parallel B} + (p(1,-1) - p(1,1)) \cdot W_e, \\
&+ (p(1,0) - p(1,1))/T_{\parallel A}
\end{aligned} \tag{31}$$

With equations (28),(29),(31) we can obtain the rate equations for P_S and P_I :

$$\begin{aligned}
dP_S/dt &= -(P_S + P_I) \cdot W_e - (P_S + 1)/T_{\parallel B}, \\
dP_I/dt &= -(P_S + P_I) \cdot W_e - P_I/T_{\parallel A}.
\end{aligned} \tag{32}$$

The steady-state saturation condition ($W_e \gg 1/T_{\parallel A}$) of the transition $|1,1\rangle \Rightarrow |1,-1\rangle$ gives rise to the equalization of the populations $p(1,1) = p(1,-1)$ and respectively to the *full nuclear spin polarization*

$$P_I = -P_S = p(0,0) = 1. \tag{33}$$

It is obvious that this state is equivalent to state of cooling up spin temperature $T_I < \hbar\omega_A/k \sim 10^{-3}$ K nuclear spins.

Let us estimate now the needed microwave power for saturation. The rate of external microwave field that induce forbidden electron transitions with frequency ω_S (for $X \approx \gamma_e \hbar B/A \leq 1$) is

$$W_e < (\gamma_e b_{\text{mw}})^2 \cdot (\overline{\Delta\omega_S^2})^{-1/2}, \tag{34}$$

where $(\overline{\Delta\omega_S^2})^{1/2} \approx 2T_{\perp S}^{*-1}$ — *nonhomogeneous broadened* resonance line widths for the saturated electron transition, b_{mw} is amplitude of *microwave field*. The quality factor Q_c of microwave cavity is

$$Q_c \approx \omega_S b_{\text{mw}}^2 \cdot V_r / (2\mu_0 P), \tag{35}$$

where V_r — volume of microwave resonator, P — dissipating power. The saturation condition is

$$W_e \gg 1/T_{\parallel S} \text{ or } (\gamma_e b_{\text{mw}})^2 T_{\perp S}^* T_{\parallel S} \gg 1, \tag{36}$$

The power dissipated in cavity is

$$P > \omega_S V_r W_e (\overline{\Delta\omega_S^2})^{1/2} / (2\mu_0 Q_c \gamma_e^2). \tag{37}$$

For example, taking $W_e \sim 10^3 \text{ s}^{-1}$, $\omega_S \sim 100 \text{ radGHz}$, $V_r \sim 1 \text{ cm}^3$, $Q_c \sim 1000$ and $(\overline{\Delta\omega_S^2})^{1/2} \sim 10^8 \text{ s}^{-1}$ [18] as a rough estimate we obtain $P > 1 \text{ mW}$. Notice that this power is applied only during the saturation process over of time $\geq W_e^{-1} \sim 1 \text{ ms}$ in the act of initializing of qubit states.

Hence, the initialization of nuclear states may be obtained by use of ENDOR technique at the lattice temperature of order 0,1 K and by this means the *the second difficulty* of Kane's scheme can be overcome.

7 A silicon-based ensemble NMR quantum computer of cellular-automaton type

For implementation of ensemble silicon quantum computer, operated on cellular-automaton principle, it may be usable the previously considered system of long chains of donor atoms ^{31}P disposed in silicon, but free of the **A** and **J** gates.

If exchange interaction constant (it is here positive) for localized electronic spins of ^{31}P along the chain is more than Zeeman energy $J(l) \gg \gamma_B \hbar B$ and the temperature is well below the critical temperature for electron ordering (Neel temperature) $T < T_{\text{NS}} \sim J(l)/k$ ($k = 1,38 \cdot 10^{-23}$ J/K — the Boltzmann constant), the one-dimensional *antiferromagnetically ordered ground state* of electronic spins is produced. We can estimate the exchange interaction constant as $J > \gamma_N \hbar B \sim 6.5 \cdot 10^{-23}$ J, that correspond to the distance between donors $l_x \sim 20$ nm [9], that is the electron spin critical temperature will be $T_{\text{NS}} \sim 4$ K.

Due to hyperfine interaction nuclear spins will be oriented according to the electronic spin direction in the resultant field and will form array with the alternating orientation of nuclear spins. At magnetic fields $B \leq A/\gamma_N \hbar \sim 3.5$ T and at temperatures $T \sim 10^{-3}$ K the nuclear spins ^{31}P will form a periodic ground state array of ABAB...type: $\uparrow\downarrow\uparrow\downarrow \dots$, where $\uparrow$ marks the ground state of nuclear spin in an A-site and $\downarrow$ — the ground state of nuclear spin in a B-site with almost 100% opposite orientation ($\omega_{A,B}/kT \geq 1$). That is the distinct nuclear spins are *in initializing ground state*.

Notice that the using of dynamic methods, makes possible the high orientation of nuclear spins also at larger temperatures and, according to the above section 5, this state will be *the long-lived nonequilibrium* nuclear spin state.

The nuclear resonant frequencies $\omega_{A,B}$ of neighbor nuclear spins are different for each of the magnetic one-dimensional subarray A and B in the chain as they depend on the states of neighboring spins. We will take it here in the simple form [12, 19]:

$$\omega_{A,B} \equiv \omega(m_{<} + m_{>}) \approx |\gamma_I \hbar B \pm A/2 - I_n(m_{<} + m_{>})|/\hbar, \quad (38)$$

where $I_n \sim (A^2/J)$ is constant of two neighbor nuclear indirect spin-spin interaction due to hyperfine interaction, $m_{<}$ and $m_{>}$ are the magnetic quantum numbers for the left and right spin subarray. The nonsecular part of nuclear-nuclear interaction is neglected here taking into account that $\gamma_N \hbar B$, $A/2 \gg I_n$. The difference between nuclear resonant frequencies for the distinct neighboring spins orientations is $\Delta\omega_I/2\pi \sim I_n/2\pi\hbar \sim (A^2/J)/2\pi\hbar \sim 0.5$ MHz, whereas the resonant nuclear frequencies are $\omega_{A,B}/2\pi \sim A/4\pi\hbar \sim 120$ MHz.

For the organization of logic operations let us use the addressing to spin states, analogously to a scheme put forward in [20]. Each nuclear spin in A-site of this scheme has *two internal* eigenstates — ground $|\uparrow\rangle$ and excited $|\downarrow\rangle$ and in B-site, accordingly, — $|\downarrow\rangle$ and $|\uparrow\rangle$.

We take into account that the life time of excited states (the longitudinal nuclear spin relaxation time $T_{||}$) at low temperatures is very long. Each *logic qubit* of quantum information in this state will be encoded here, similar to [20], by the *four states* of *physical spin-qubits* (individual nuclear spin states): the logical qubit basis state "0" will be encoded by unit $|\downarrow\uparrow\uparrow\downarrow\rangle$, while the state "1" — by $|\uparrow\downarrow\downarrow\uparrow\rangle$. It is important here that the resonant frequencies of nuclear spins depend on neighbor spins states. Both logical states have two excited spin states and the *zero projection* of total nuclear spin.

Notice that a random inversion of only one spin will result in degradation of the qubit state. But to form the rough error, for example, of "0" $\Rightarrow$ "1" type in the coding of stored quantum information it is essential to invert *simultaneously four* spins. Therefore, it may be concluded that

the considered way of qubit coding ensures *a better fault-tolerance* with respect to this type of errors.

As the *ports* (noted on Fig. 5 by $\times$) for input and output of the information in the array of ground states spin-qubits can be dopant nuclei D at the certain place of the array with distinct resonant frequency, defects or local gates that modify the resonant frequency of the nearest nuclear spin in the array.

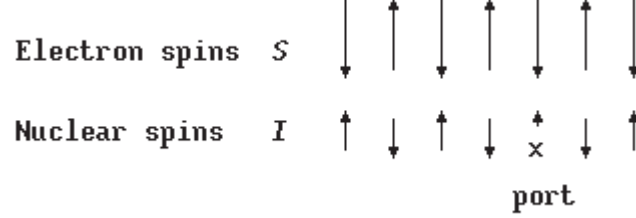


Fig. 5. Scheme of electron and nuclear spins ordering

Starting from the perfectly initialized states inputting the information can be performed by setting the dopant D-spin to a desired state by means of RF-pulse at its resonant frequency. The nuclear spin state of spin nearest to the dopant spin is created by SWAP operation. After the required information is loaded, D-spin is reset to the ground state. Upon completion of computation, the state of any spin can be measured by moving it to the A-site nearest to D, then swapping $A \Rightarrow D$ and finally measuring the state of D-spin.

For the implementation of quantum operations on logic qubits we will also introduce, as in (19), one auxiliary *control unit* (CU), which is represented here by *six* physical spin states in the pattern $\uparrow\downarrow\downarrow\uparrow\uparrow\downarrow$. The CU exists only in one place along the array and is separated from logical qubits by odd number of spacer spins. The applying corresponding SWAP sequence of pulses CU leads to interaction of CU with one and two logical qubits and performing on them one- and two-qubit quantum operations (for more details, see [12, 19]).

In the case of a large enough ensemble of in parallel acting chains the states may be measured by NMR methods. For the increasing of logic qubit number in single "molecule" to $\geq 10^3$, that falls on one port, it can be used two- and three-dimensional structures with antiferromagnetic chess-type ordering of electron spins. The corresponding ordering will have and for nuclear spins (Fig. 6).

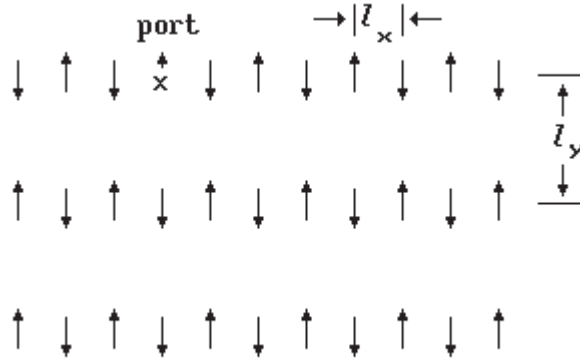


Fig. 6. Scheme of two dimensional ordering of initialized nuclear spins.

If, for example, the number of spins-qubits, falls on one port in linear chain is, say, $L \sim 30$, so in two-dimension case their number will be $L = 900$. Ensemble that is composed of $N \sim 10^5$ in parallel acting such plane "artificial molecules" permit to provide input and output of information through the standard NMR techniques. The using of more sensitive ENDOR techniques has particular meaning when it may be combined with the techniques of dynamic polarization (solid state effect).

The advantage of ensemble quantum cellular automaton in the comparison with the above considered ensemble variant with strip gates is as follows:

a) The system of the control gates is absent, what essentially simplifies the producing of computer structure and eliminates one of the important source of decoherence.

b) The coding of logic qubits into four physical qubits gives a higher degree of fault-tolerance in logic operations.

It follows that the going to ensemble quantum cellular automaton permits to overcome *the third and fourth* difficulty of Kane's scheme.

The main disadvantage of cellular automaton scheme is the relative complexity of logic operation performing.

Notice here that there is also an another possibility of the ensemble NMR implementation, which does not have the gate system. The selectivity of nuclear resonance frequencies for individual qubits in the chain ensemble can be achieved, instead of $\mathbf{A}$ -gates voltage, by applying the external magnetic field gradients along axis x for neighbour qubits separated by ~ 20 nm of order $dB_z/dx \sim 1$ T/cm (that is feasible now), which produce a ~ 100 Hz resonance frequency difference.

8 Decoherence of the qubit quantum states in an ensemble register

The interaction of nuclear spins-qubits with polarized *random distributed* paramagnetic centre (atoms and defects) in substrate causes a spread of resonance frequencies for distinct qubits, determined by the dipole-dipole electron-nuclear spin interaction. For low temperatures ($T \leq 0,1$ K) it is the main mechanism of *nonhomogeneous broadening* of nuclear resonance line widths $(\Delta\omega_I^2)^{1/2}$. Therefore for its elimination it is required to use the *cleaning* from such centres.

To estimate the allowed concentration of paramagnetic centres in silicon substrate C_S we will take the expression

$$(\overline{\Delta\omega_I^2})^{1/2} \sim \mu_0/(4\pi) \cdot \gamma_N\gamma_B\hbar C_S \geq 1/T_{\perp I} \gg 1/T_{\parallel I}, \quad (39)$$

where $T_{\perp I}$ — the homogeneous nuclear spin transverse relaxation time, which correspond to *decoherence time* τ_D of nuclear quantum states. This time to be *sufficiently large* (~ 1 s) as compared with the RF control pulses length ($\sim 10^{-5}$ s) in order one can be done in a time of order τ_D a necessary for large-scaled computing number of logic operation ($> 10^5$) [15].

Taking into account that frequency of interqubit indirect interaction $\nu_J \approx 100$ kHz (see above), for the *coherence length* of quantum register state we obtain $\lambda \sim 2\pi\Delta\nu l_x \cdot \tau_D \approx 6.3 \cdot 10^5 \cdot l_x$.

With $\tau_D = 1$ we obtain for the allowed concentration of paramagnetic centers the estimate $C_S < 10^{15} \text{ cm}^{-3}$, that is *almost usual* requirement for *a degree of cleaning* from unwanted impurities in silicon technology.

The another mechanism of decoherence of qubit states is the dipole-dipole interaction with *nuclear spins* of impurity atoms of nuclear spin containing elements.

The *allowed concentration* C_N of impurity with nuclear spins in silicon substrate can be estimated from the following expression

$$\tau_D > ((\mu_0/4\pi) \cdot \gamma_N^2 \hbar \cdot C_N). \quad (40)$$

Taking again $\tau_D \sim 1$ s, we will obtain $C_N < 2 \cdot 10^{18} \text{ cm}^{-3}$. For the number of silicon atom $5.0 \cdot 10^{22} \text{ cm}^{-3}$ the allowed relative concentration of the impurity nuclear spin, contained isotope ^{29}Si , must be $C_N\% < (2 \cdot 10^{18} \cdot 100)/(5.0 \cdot 10^{22}) = 0.4 \cdot 10^{-2}\%$. For comparison, the natural abundance of isotope ^{29}Si in natural silicon is 4.7%. At present the realized degree of cleaning ^{28}Si is 99,98%, which is yet *not sufficient* to our purposes.

The allowed concentration for another impurity elements having the natural abundance of isotopes with nuclear spins $P < 100\%$ is determined from

$$C_N\% < 10^{-2}100/P. \quad (41)$$

In the case of ensemble approach for implementing of logic quantum operations, for read-out of information and for suppressing of decoherence effects, caused by secular part of dipole-dipole interaction qubits with randomly distributed paramagnetic centres, may be explored the well known *many-pulsed technique of high resolution NMR spectroscopy in solids* [21].

As source of errors in quantum computer operation there is also generation processes unwanted states for neighbour initialized qubits as a result of nonresonance effects. This is a further mechanism of the decoherence of quantum states. The probability of such errors can suppress to the required value ($< 10^{-5}$) by choosing of Rabi frequency value for control RF-pulses [22]. For one example, if resonance frequencies of nonresonant qubits differ from the frequency of resonant qubit by $\Delta\omega$, so the Rabi frequency for π -pulse should be $\Omega = |\Delta\omega|/\sqrt{4k^2 - 1}$, where $k = 1, 2, 3, \dots$

Notice that it was also suggested another, as compared to considered above, scheme of the four-spin encoding two logical qubits, which are represented by the two zero-total spin states of four spins, generated by the pairs respectively of the singlet and triplet states [23]. This scheme is based on the so named *collective decoherence conditions*. This conditions can be attained in coupled spins at very low temperatures, when the longest wavelength magnon modes are quenched [12, 19].

The *chief disadvantage* of the variant with strip gates as and Kane's scheme is associated with availability of the gates. The thermal voltage fluctuations on gates are additional mechanism of quantum state decoherence. They are essentially suppressed here if both the Al gate electrodes and the entire resonance circuit are superconductors at the work temperature $T < T_C$ ($T_C = 5.8$ K for films).

Conclusion

1) The line of the large-scale ensemble NMR quantum computer development have certain advantage over the line, based on Kane's scheme. It consists in the possibility of employment of the standard NMR technique for the measurement of quantum states at output of computer, like in the liquid prototype.

2) For the initialization of nuclear spin states at temperature $T \sim 0,1$ K methods of dynamic polarization of solid state effect type may be proposed.

3) Analysis of proposed planar structure of ensemble silicon computer shows the possibility of realization of large-scale NMR quantum computer for ensemble component number $N \sim 10^5$.

4) The implementation of cellular automaton principle permits to abandon the realization regular nanostructure in form of gate chains.

5) Analysis of different feasible ways for to obtain a decoherence times large enough shows that the values, needed to perform required for large-scaled computations number of quantum logic operations $\sim 10^5$, can be achieved.

6) One would expect, that in the future the combined variants of solid state quantum computers will be proposed. They can, say, exploit the structures that are contained nuclear spins and quantum dots with electron spins and the combined methods access to qubits, like ENDOR method.

Appendix

Signal NMR for discrete ensemble of nuclear spins

Let us consider here the sample that involves $N = nL \cdot pN_0$ nuclear spins arranged in the plane $z = 0$ of the silicon plate at regular intervals along the strips (Fig. 4). The spins in chains under strip at resonance in the each block are oriented along x axis (solenoid axis) and separated at intervals of L . The read out NMR signal is

$$|V_{\max}| = Q\omega_A \frac{K}{X} \int_{-X/2}^{X/2} \left| \int_A B_{\text{xmax}}(x, y, z) dy dz \right| dx, \quad (42)$$

where $X = nL \gg L$ is roughly the length of solenoid and

$$B_{\text{xmax}}(x, y, z) = \quad (43)$$

$$= \frac{\mu_0 \gamma_I \hbar}{16\pi} \sum_{n_i=-n/2}^{n/2} \sum_{p_i=-pN_0/2}^{pN_0/2} \frac{-2(x - Ln_i)^2 + (y - l_y p_i)^2 + z^2}{[(x - Ln_i)^2 + (y - l_y p_i)^2 + z^2]^{5/2}} \quad (44)$$

is the peak magnetic field produced by resonant spins in solenoid. For simplicity it is suggested that $n, p, N_0, L \gg 1$ are the even numbers. We assume that the area of coil turns is $A = D \cdot \delta$ ($D = l_y \cdot pN_0$, $\delta \ll D$).

For summation over n_i and p_i we have used the *Poisson's summation formula*, namely,

$$\sum_{p_i=-pN_0/2}^{pN_0/2} f(l_y p_i) = \frac{pN_0}{D} \sum_{\nu=-\infty}^{\infty} \int_{-D/2}^{D/2} f(\xi) \exp(i\nu 2\pi \xi / l_y) d\xi, \quad (45)$$

by omitting the oscillated terms with $\nu \neq 0$:

$$|V_{\max}| = \mu_0 Q K \omega_A \frac{\gamma_I \hbar}{8\pi} \frac{1}{X} \int_{-X/2}^{X/2} dx \frac{n}{X} \int_{-X/2}^{X/2} d\eta \cdot \int_0^{\delta/2} dz \left| \frac{pN_0}{D} \int_{-D/2}^{D/2} \int_{-D/2}^{D/2} \frac{-2(x - \eta)^2 + (y - \xi)^2 + z^2}{[(x - \eta)^2 + (y - \xi)^2 + z^2]^{5/2}} dy d\xi \right| \quad (46)$$

Taking into account $D^2 \gg z^2$, upon integrating (A.4) over y, ξ , we obtain

$$|V_{\max}| = \mu_0 Q K \omega_A \frac{\gamma_I \hbar}{8\pi} \frac{pN_0}{D} \frac{1}{X} \int_{-X/2}^{X/2} dx \frac{n}{X} \int_{-X/2}^{X/2} d\eta \cdot$$

$$\int_0^{\delta/2} dz \left\{ \frac{2[(x-\eta)^2 - z^2]D^2}{[(x-\eta)^2 + z^2]^2[D^2 + (x-\eta)^2]^{1/2}} + \frac{2z^2}{[(x-\eta)^2 + z^2]^{3/2}} \right\}. \quad (47)$$

By integrating now over z and preserving only the major logarithmically increasing for $2|x-\eta|/\delta \Rightarrow 0$ term, we obtain

$$\begin{aligned} |V_{\max}| &\approx \mu_0 QKA\omega_A \frac{\gamma_1 \hbar}{4\pi} \frac{npN_0}{AD} \frac{1}{X} \int_{-X/2}^{X/2} dx \frac{1}{X} \int_{-X/2}^{X/2} d\eta \log \frac{\delta}{|x-\eta|} = \\ &= (\mu_0/4) QKA\omega_A \frac{N}{V_s} \gamma_1 \hbar \cdot \frac{X}{\pi D} \log \frac{X}{\delta \sqrt{e}}, \end{aligned} \quad (48)$$

where $V_s = AX$, $N = npN_0$, $e = 2,718 \dots$

We see that expression (48) is distinguished from (4) by non-essential factor $\frac{X}{\pi D} \log \frac{X}{\delta \sqrt{e}}$, that is of order several ones.

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